
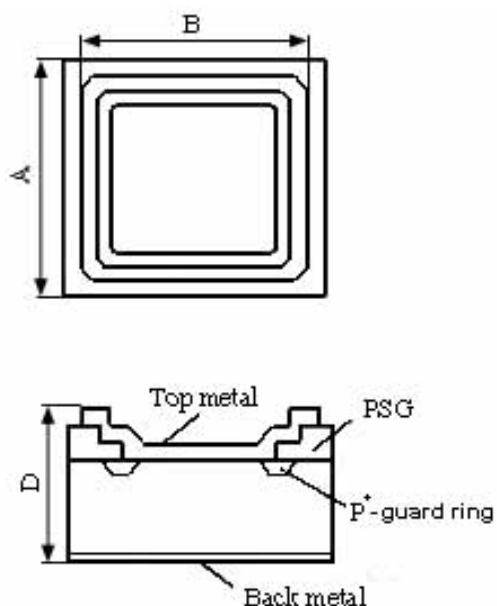


# SCHOTTKY DIODES KDS 2127G. PRELIMINARY



Rev.1. Feb. 2010

 <b>VSP-MIKRON</b>	<b>0,5A/40V. Die Size-39mil.</b>			
Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10\text{mA}$	$V_{BR}$	V	40	45
Average Rectified Forward Current	$I_{F(AV)}$	A	0,5	-
DC Forward Voltage @ $25^\circ\text{C}$ , $I_F=0,5\text{A}$	$V_F$	V	0,36	0,34 (0,33-typ)
Maximum Reverse Current  @ $25^\circ\text{C}$ , $V_R=40\text{V}$ $25^\circ\text{C}$ , $V_R=45\text{V}$ $100^\circ\text{C}$ , $V_R=40\text{V}$	$I_R$	mA	0,50 - 15,0	0,40 0,50 13,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	$I_{FSM}$	A	40	-
Peak Repetitive Reverse Surge Current @ $2,0\mu\text{s}$ , $f=1\text{kHz}$ ., $T_J<125^\circ\text{C}$ .	$I_{RRM}$	A	1,5	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	$\pm 8$ (contact)	
Voltage Rate of Change	$dV/dt$	$\text{V}/\mu\text{S}$	10.000	
Operating Junction Temperature	$T_J$	$^\circ\text{C}$	125	



DIM	ITEM	$\mu\text{m}$
$A_x$ $A_y$	Wafer Form Die Size	1000 1000
$B_x$ $B_y$	Top Metal Size	820 820
D	Thickness	300max.
Scribe line Width		80

*Top metal:* a) **Al** – for Wire Bonding;  
b) **Al-Ni-Ag** – for Soldering.  
*Backside metal:* **Ti-Ni-Ag**.